NSN 5961-01-121-1073

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View Online at https://aerobasegroup.com/nsn/5961-01-121-1073

Inclosure Material:
Metal
Overall Length:
0.675 inches
Overall Height:
0.370 inches
Overall Width:
0.625 inches
End Application:
An/wlq- (v) 07397
Mounting Facility Quantity:
1
Internal Configuration:
Junction contact
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-228
Mounting Method:
Threaded stud
Features Provided:
Hermetically sealed case
Thread Size:
0.250 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
210.0 breakdown voltage, collector to emitter, with specified voltage between base and emitter and 200.0 breakdown voltage,
collector-to-emitter, base open and 6.0 breakdown voltage, emitter-to-base, collector open
Current Rating Per Characteristic:
6.00 amperes source cutoff current
Power Rating Per Characteristic:
100.0 watts small-signal input power, common-collector preset
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius junction
Special Features:
Junction pattern arrangement: pnp
Precious Material And Location:
Terminals and stud surfaces gold
Precious Material:
Gold
Test Data Document:
03640-6086937 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.;

excludes any specification, standard or other document that may be referenced in a basic governing drawing)

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Thread Series Designator:

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3 uninsulated wire lead

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0